
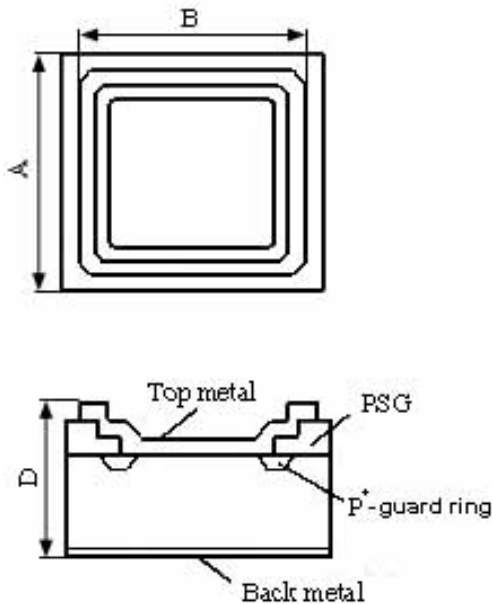


SCHOTTKY DIODES KDN-20060.



Rev.1. Feb. 2010

 VSP-MIKRON		20A/60V. Die Size-106*138mil.		
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	20,0	-
DC Forward Voltage @ 25°C, $I_F=20,0A$	V_F	V	0,65	0,63
Maximum Reverse Current @ 25°C, $V_R=65V$ 25°C, $V_R=60V$ 125°C, $V_R=60V$	I_R	mA	- 0,350 200,0	0,350 0,300 190,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	250	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150°C$.	I_{RRM}	A	4,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	µm
A_x A_y	Wafer Form Die Size	2700 3500
B_x B_y	Top Metal Size	2560 3360
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
 b) **Al-Ni-Ag** – for Soldering.
 Backside metal: **Ti-Ni-Ag**.